

OTA Design Using g_m/i_d Method in Open-Source GF180MCU Process

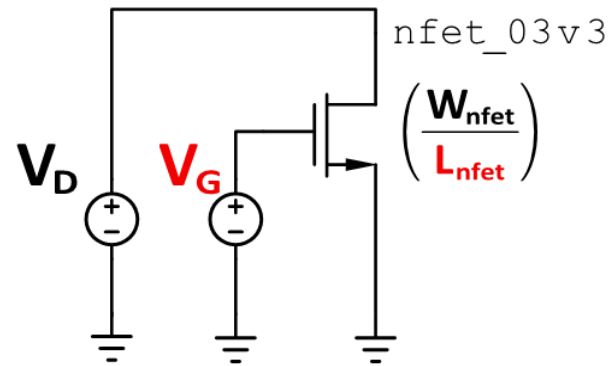
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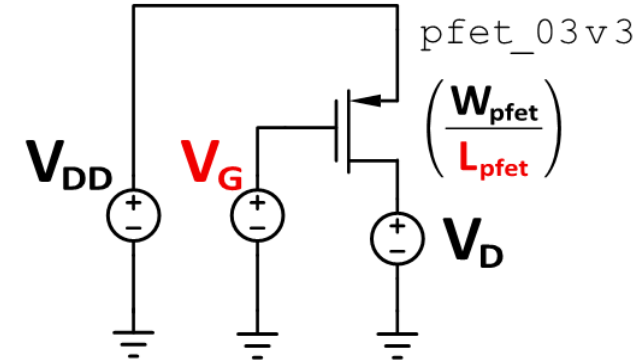
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Creating LUT

NMOS Testbench



PMOS Testbench

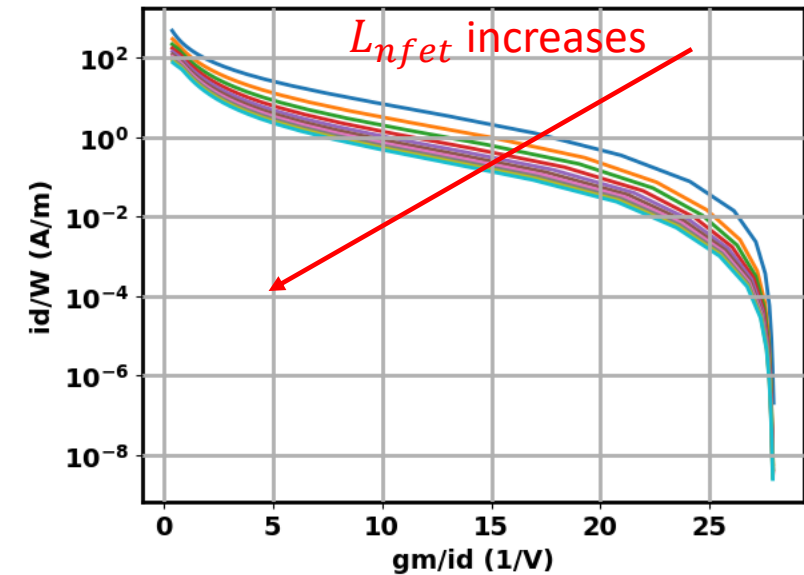
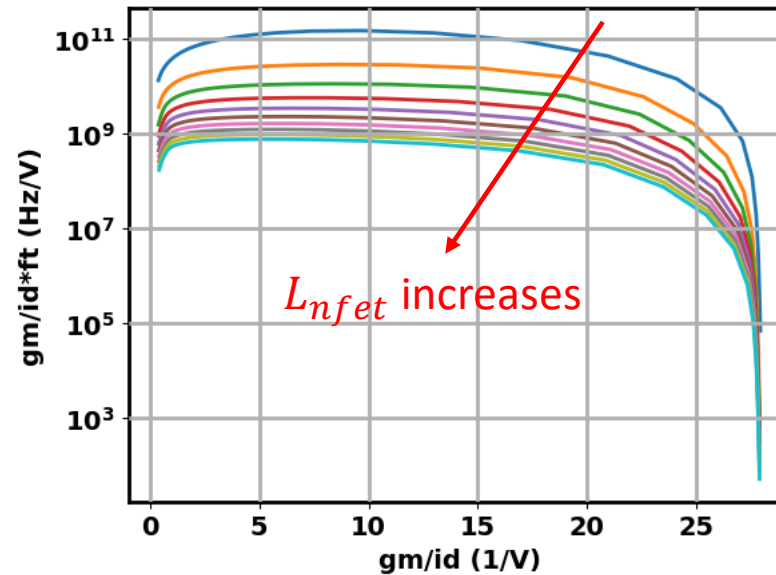
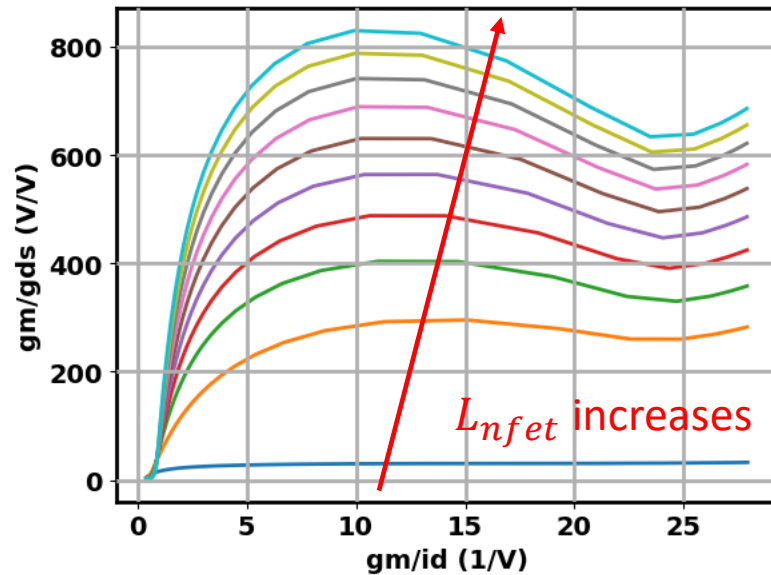


- In GF180MCU, $V_{DD} = 3.3\text{ V}$
- In both testbenches:
 - Set $V_D = \frac{V_{DD}}{2} = 1.65\text{ V}$, $W_{nfet} = 4\text{ }\mu\text{m}$ (which does not matter here, can be any other reasonable value)
 - Sweep V_G from 0 to 3.3 V (step size up to you)
 - Sweep L_{nfet} from 0.28 μm to 0.4 μm (step size up to you)

Creating LUT

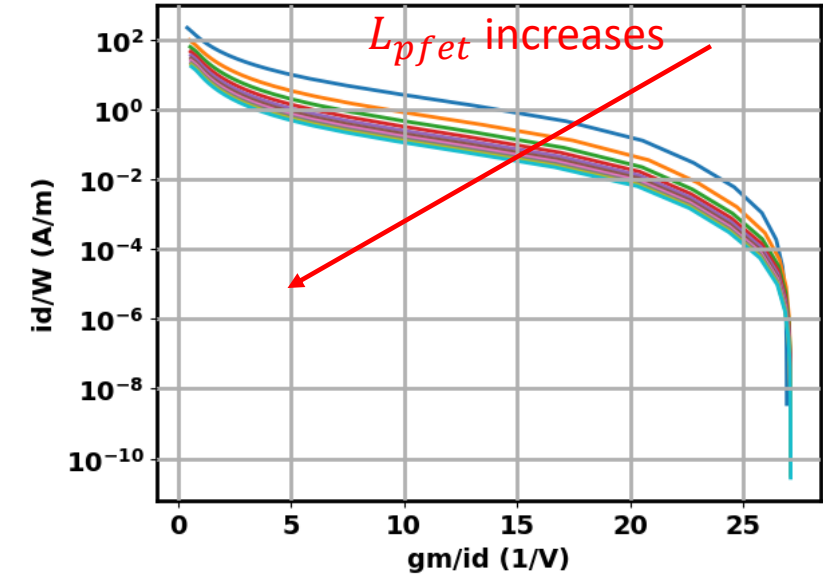
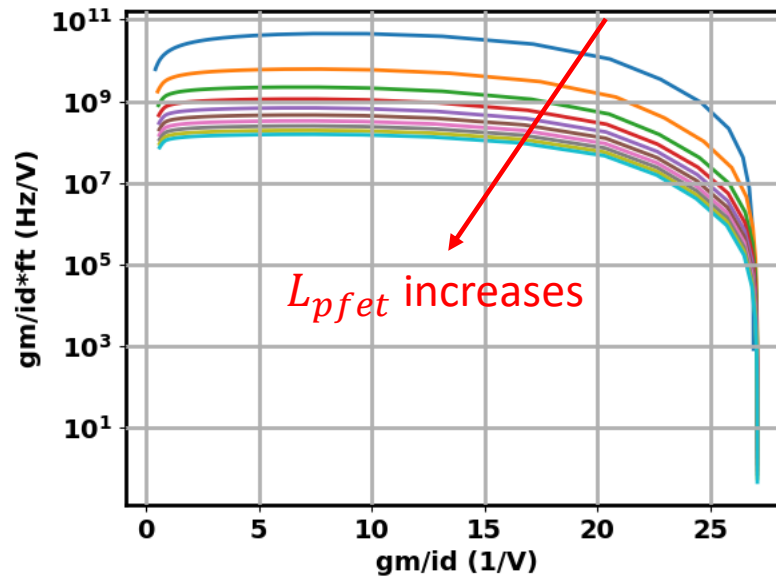
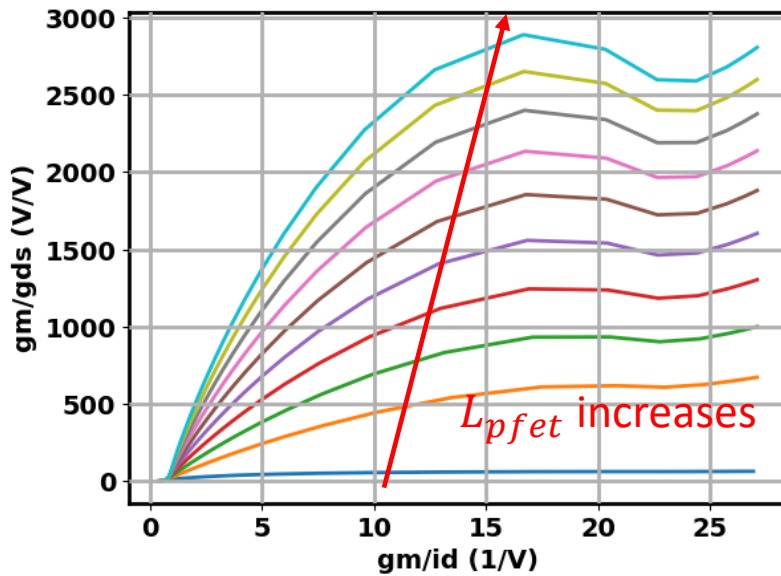
- Generating three key plots:
 - i_d/W vs g_m/i_d (current density, tells you the efficiency of how much current you pay for the transconductance; used for sizing purpose)
 - g_m/g_{ds} vs g_m/i_d (for gain requirement)
 - $f_t * g_m/i_D$ vs g_m/i_d (for best GBW requirement, usually it tells the optimal g_m/i_D range)

Creating LUT - NMOS



- Increasing L will increase the gain
- Increasing L will decrease f_t
- Increasing L will decrease current density

Creating LUT - PMOS

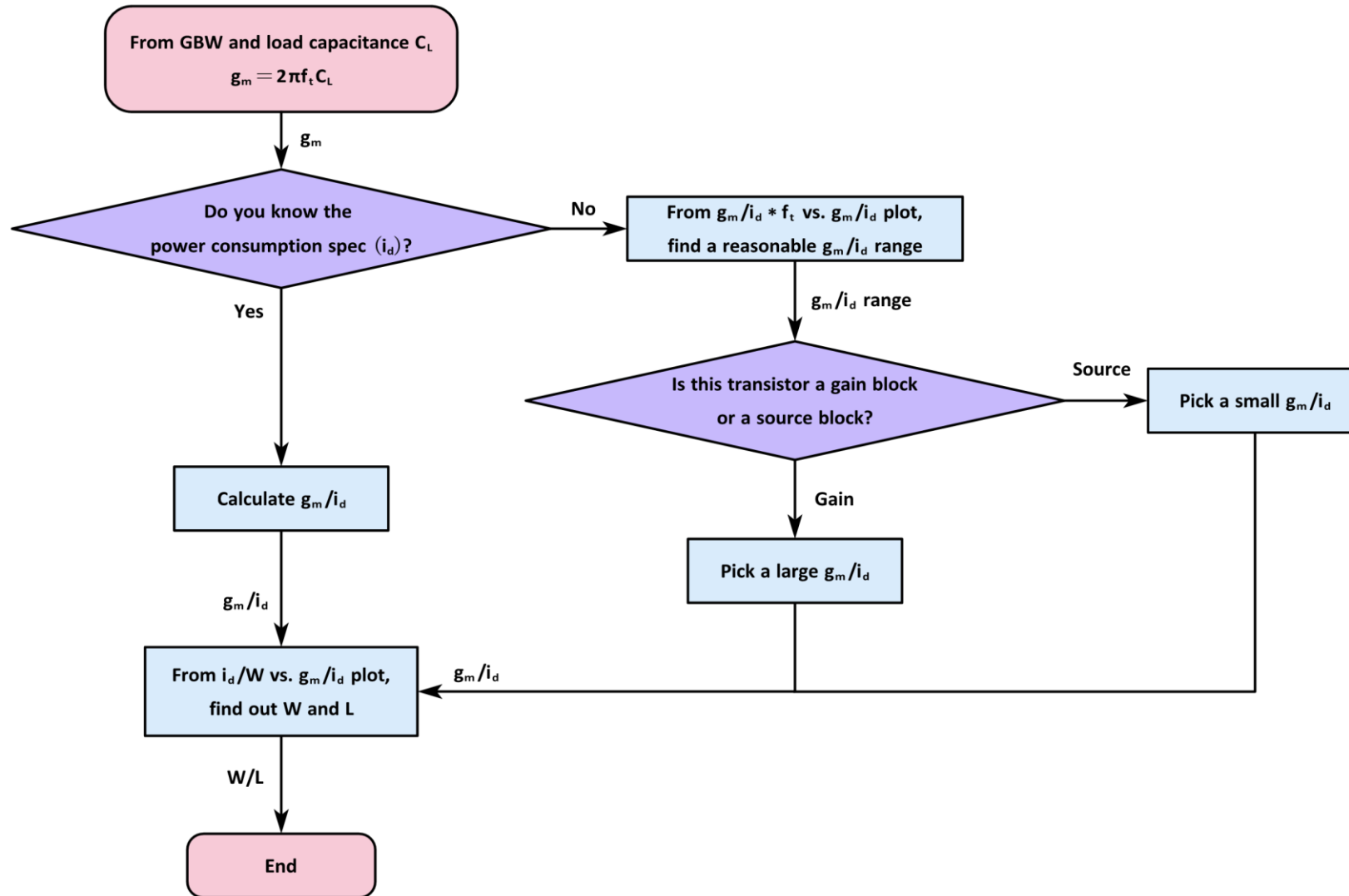


- With same g_m/i_d , PMOS has higher intrinsic gain than NMOS
- With same g_m/i_d , PMOS is slower than NMOS
- With same g_m/i_d , PMOS has lower current density

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Simplified Design Algorithm Using g_m/i_d Method



Choice of large and small g_m/i_d

- Why you want large g_m/i_d for gain stage, but small g_m/i_d for biasing/source?
- Transistor current noise: $\overline{I_{n,M_1}^2} = 4kT\gamma g_{m,M_1} \approx \frac{8}{3}kT g_{m,M_1}$
 - The larger g_m , transistor itself is noisier. When it is used as a current source, we want the noise smaller, therefore smaller $\frac{g_m}{i_d}$.
- When this noise is input-referred:
 - $\overline{V_{n,out}^2} = \overline{I_{n,M_1}^2} r_{o,M_1}^2 \approx \frac{8}{3}kT g_m r_{o,M_1}^2$
 - $\overline{V_{n,in}^2} = \frac{\overline{V_{n,out}^2}}{g_{m,M_1}^2 r_{o,M_1}^2} \approx \frac{8}{3} \frac{kT}{g_{m,M_1}}$
 - Therefore, when it is used as a gain stage, by increasing g_m , the input-referred noise is decreasing.

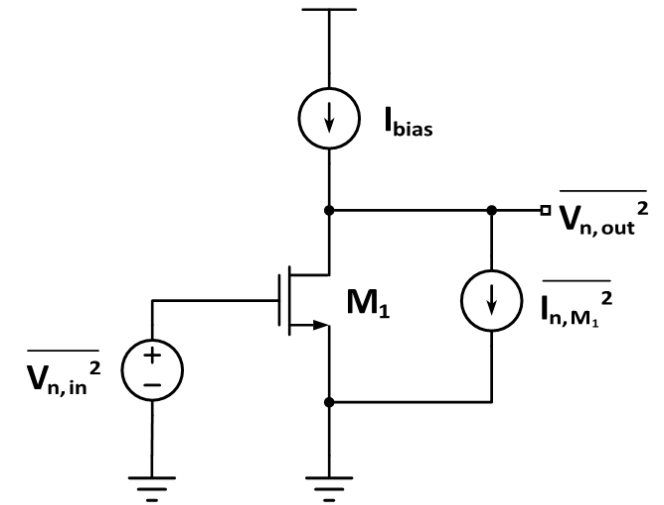
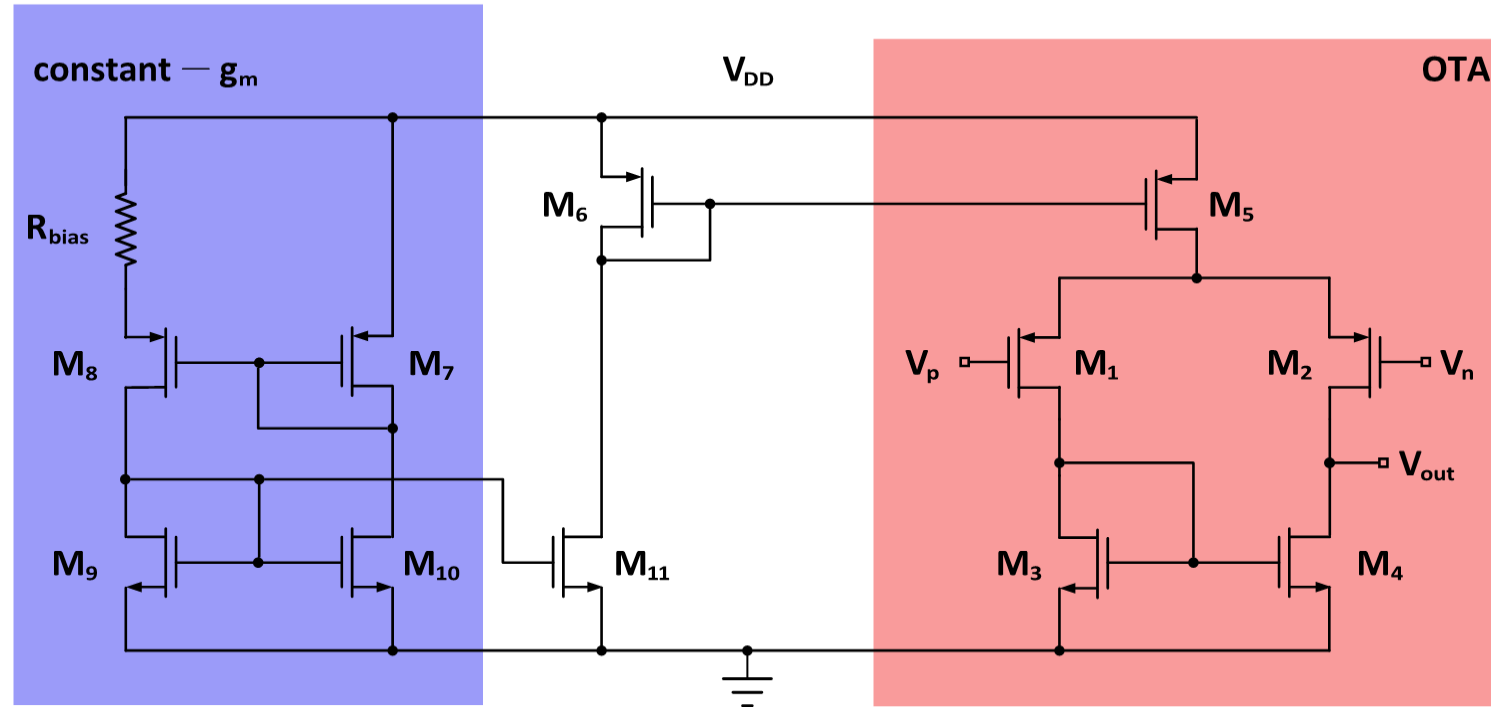


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Design Example: Diff-pair with Constant- g_m Biasing



- Specifications:
 - $GBW = 20 \text{ MHz}$
 - $C_L = 10 \text{ pF}$

Design Example: Diff-pair with Constant- g_m Biasing

- Start with M_1 (and M_2)
 - From C_L and GBW : $g_{m,M_1} = 2\pi f_t(1 + 0.2)C_L \approx 1.5 \text{ mS}$
 - The factor 0.2 is to capture some parasitic capacitance
 - Since we don't have a specific power consumption spec here, we pick $g_m/i_d = 15$ for M_1 since it is a gain stage.
 - Calculate i_d : $i_d = \frac{g_{m,M_1}}{g_m/i_d} = \frac{1.5 \text{ mS}}{15} = 100 \text{ }\mu\text{A}$
 - From i_d/W vs. g_m/i_d plot (LUT) of PMOS, we determine (there could be some other different candidates) $W_{M_1} = 80 \text{ }\mu\text{m}$, $L_{M_1} = 280 \text{ nm}$
 - If you have any DC gain requirement, you can increase L_{M_1} by looking at g_m/g_{ds} vs. g_m/i_d plot, which will give you a new W_{M_1} .

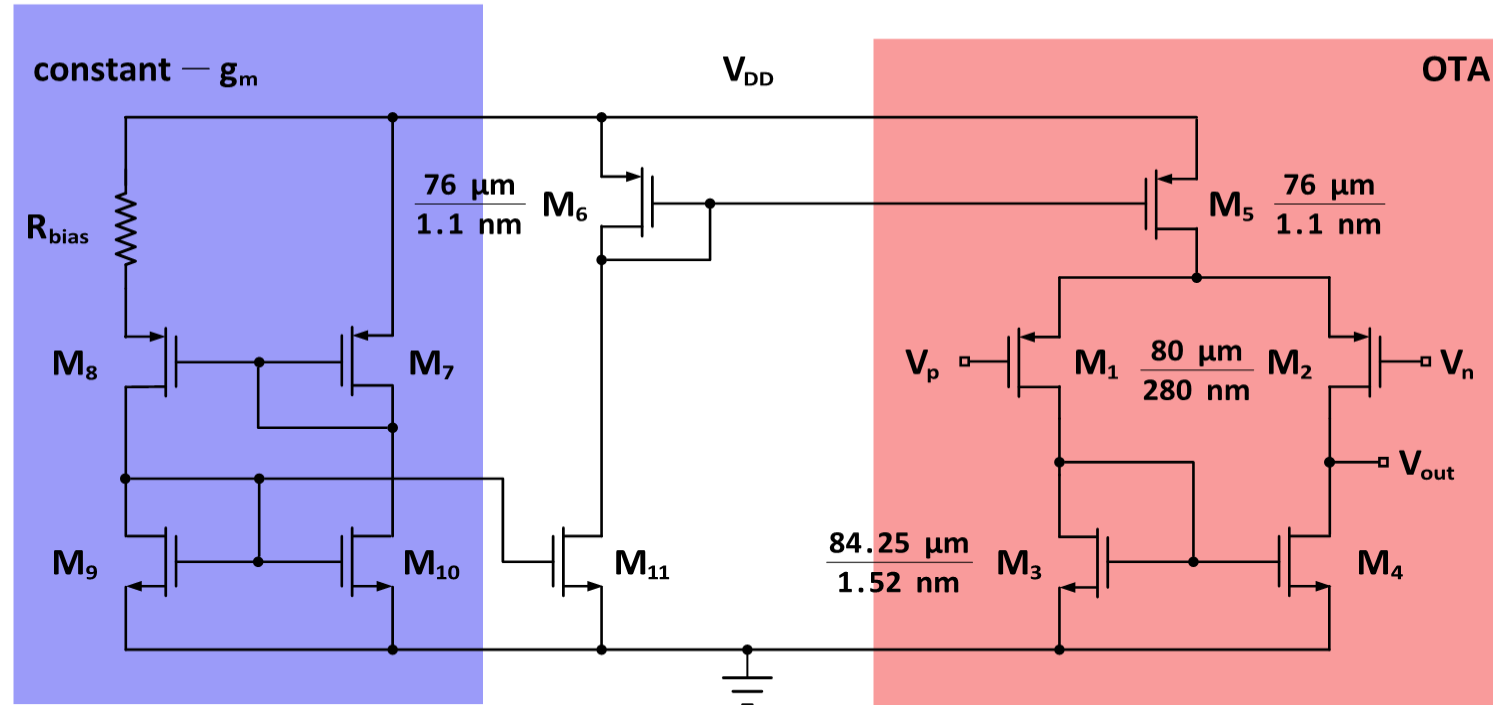
Design Example: Diff-pair with Constant- g_m Biasing

- Second, we design M_3 (and M_4)
 - Since we don't have a specific power consumption spec here, we pick $g_m/i_d = 10$ for M_3 since it is active load (source), so it should be smaller.
 - Since we know $i_{d,M_3} = i_{d,M_1} = 100 \mu A$ already from the calculation of M_1 , from i_d/W vs. g_m/i_d plot (LUT) of NMOS, we determine (there could be some other different candidates) $W_{M_3} = 84.25 \mu m$, $L_{M_1} = 1.52 \mu m$
 - The active load and current source shall have larger output impedance, therefore L is intentionally picked larger value.

Design Example: Diff-pair with Constant- g_m Biasing

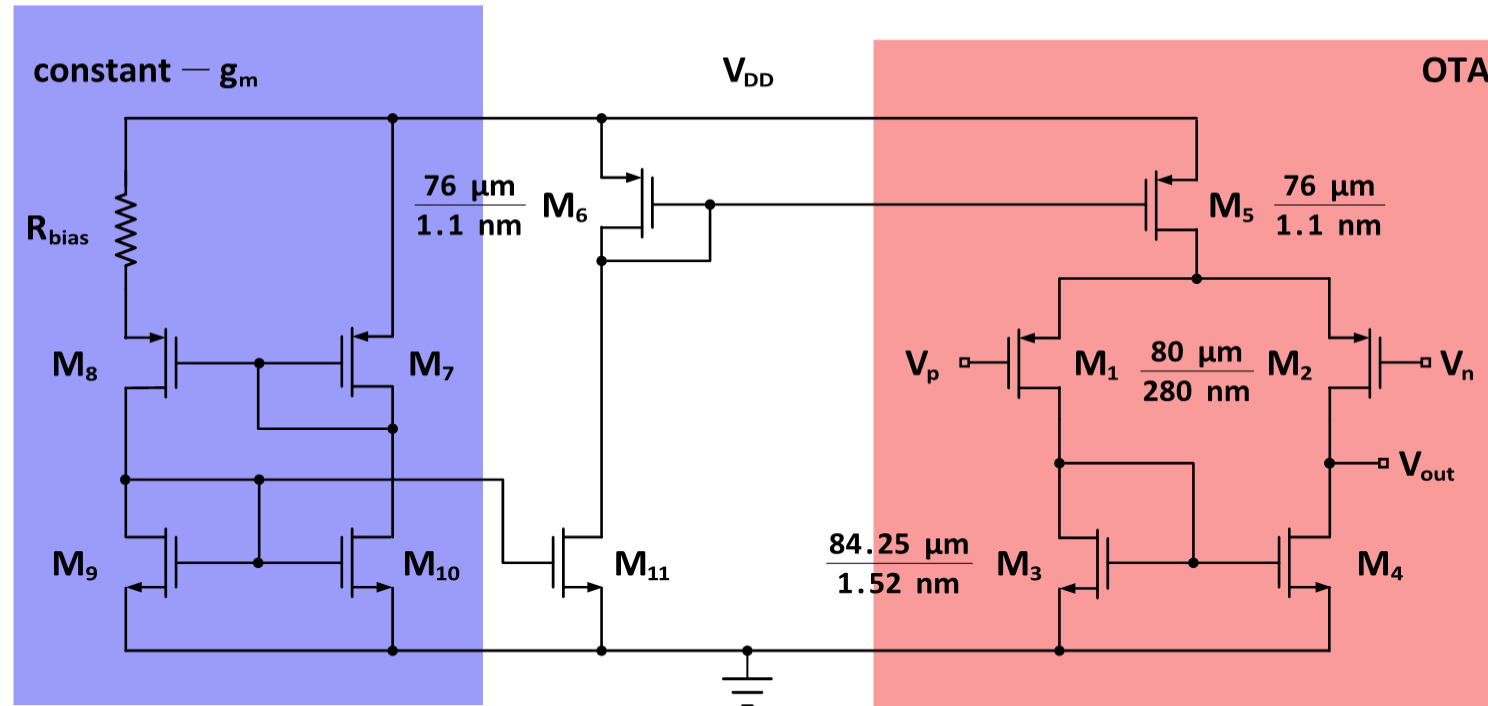
- Third, we design current mirror M_5 (and M_6)
 - For simplicity here, we assume M_5 and M_6 have the same dimension (can be scaled down later for reducing power consumption).
 - Since we don't have a specific power consumption spec here, we pick $g_m/i_d = 4$ for M_5 since it is active load (source), so it should be smaller.
 - The g_m/i_d is even smaller than M_3 's since here, $i_{d,M_5} = 2i_{d,M_3}$, smaller g_m/i_d can give larger L values, which is desirable for current mirror design.
 - Since we don't have a specific power consumption spec here, we pick $g_m/i_d = 4$ for M_5 since it is active load (source), so it should be smaller.
 - Since we know $i_{d,M_5} = 2i_{d,M_1} = 200 \mu A$ already from the calculation of M_1 , from i_d/W vs. g_m/i_d plot (LUT) of PMOS, we determine (there could be some other different candidates) $W_{M_5} = 76 \mu m$, $L_{M_5} = 1.1 \mu m$

Design Example: Diff-pair with Constant- g_m Biasing



- Now, we start designing constant- g_m block

Design Example: Diff-pair with Constant- g_m Biasing



- Ideally, $g_{m,M_7} = \frac{1}{R_{bias}}$ if $W_{M_8} = 4W_{M_7}$
- If we let M_1 and M_7 have the same size, and if we can somehow let M_1 and M_7 have the same g_m , then their i_d will also be the same.

Design Example: Diff-pair with Constant- g_m Biasing

- Design R_{bias} :

- Letting $g_{M_1} = g_{M_7}$: $g_{M_1} = \frac{g_m}{i_d} \times i_{d,M_1} = 1.5 \text{ mS} = g_{M_7}$

- $R_{bias} = \frac{1}{g_{M_7}} = 667 \text{ } \Omega$

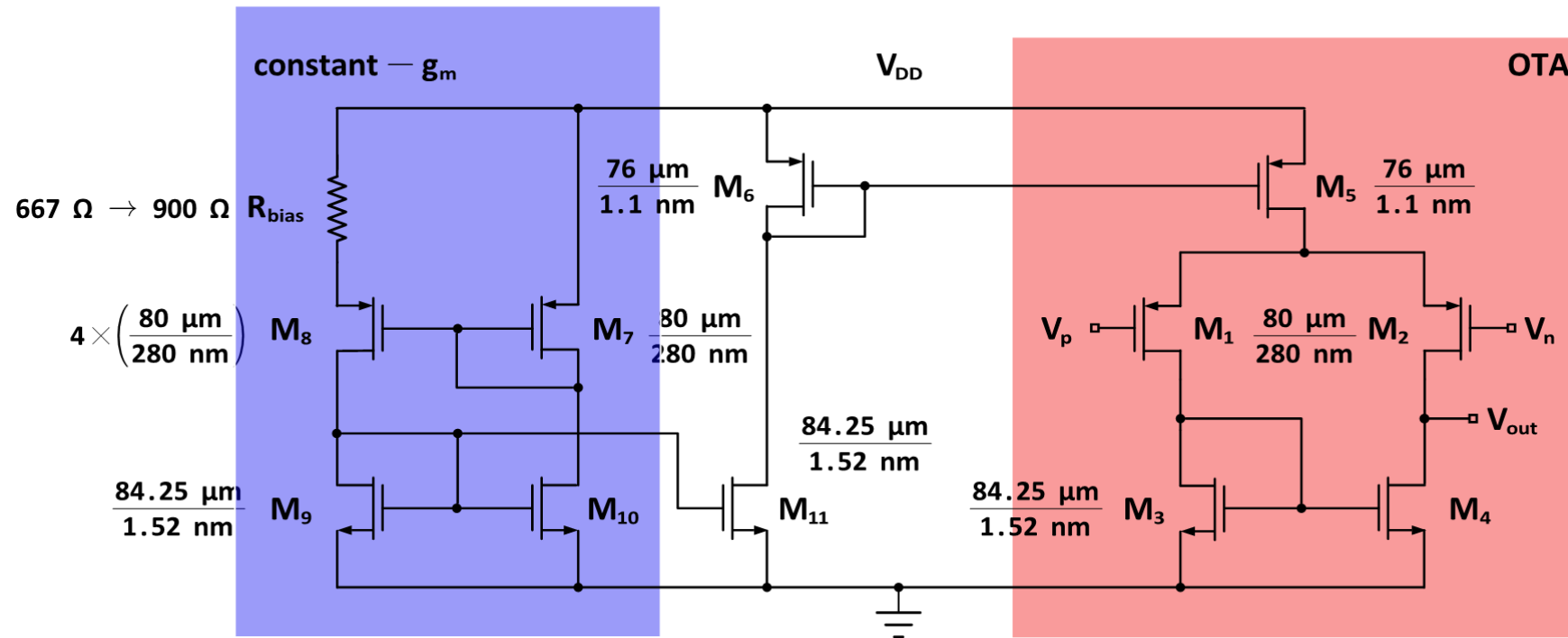
Design Example: Diff-pair with Constant- g_m Biasing

- Design M_7 (and M_8):
 - Simply copying M_1 to M_7 : $W_{M_1} = W_{M_7} = 80 \mu m$; $L_{M_1} = L_{M_7} = 280 nm$
 - Rather than making $W_{M_8} = 4W_{M_7}$, we can let $W_{M_8} = W_{M_7}$ and use multiplier: $M_{M_8} = 4M_{M_7}$

Design Example: Diff-pair with Constant- g_m Biasing

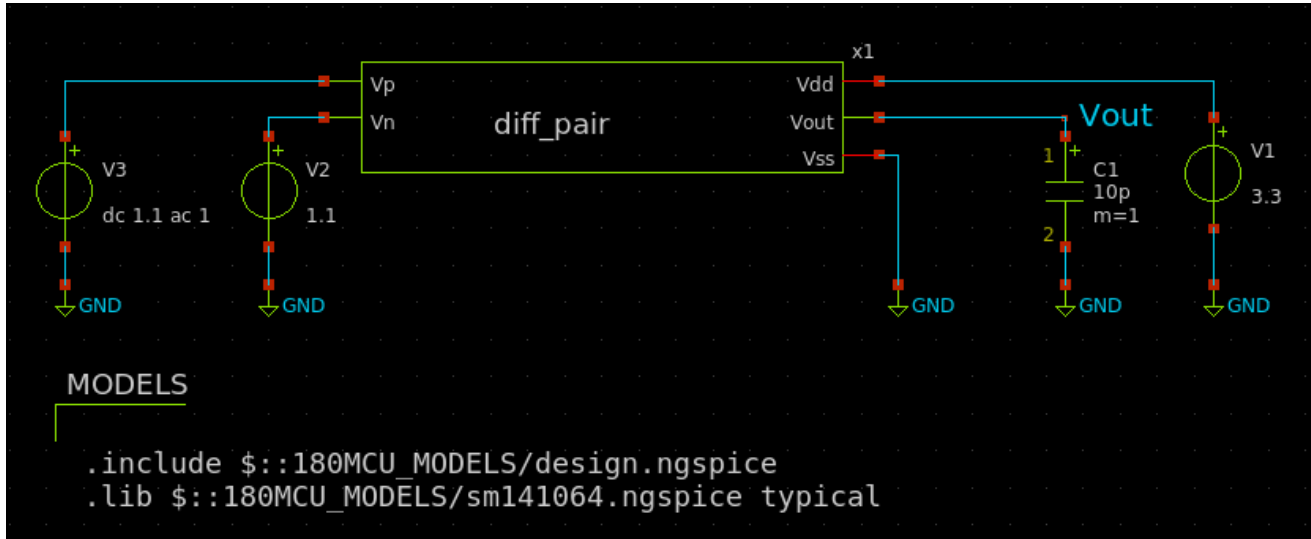
- Design M_9 (M_{10} and M_{11}):
 - Simply copying M_3 to M_9 , M_{10} and M_{11}
 - If necessary, you can increase L of M_9 , M_{10} and M_{11} to increase the output resistance of current mirror
 - Ensure you are always operating them in saturation region!

Design Example: Diff-pair with Constant- g_m Biasing



- Small fine tune is needed on R_{bias} (from $667\ \Omega$ to $900\ \Omega$) to achieve more accurate results

Results



params	gm/id method	SPICE simulation
Id_M1 (uA)	100.53	102.69
Id_M3 (uA)	100.53	102.69
Id_M5 (uA)	201.06	205.38
gm/id_M1 (1/V)	15.00	12.86
gm/id_M3 (1/V)	10.00	10.66
gm/id_M5 (1/V)	4.00	4.23
gain (dB)	34.62	35.69
GBW (MHz)	20.00	19.95

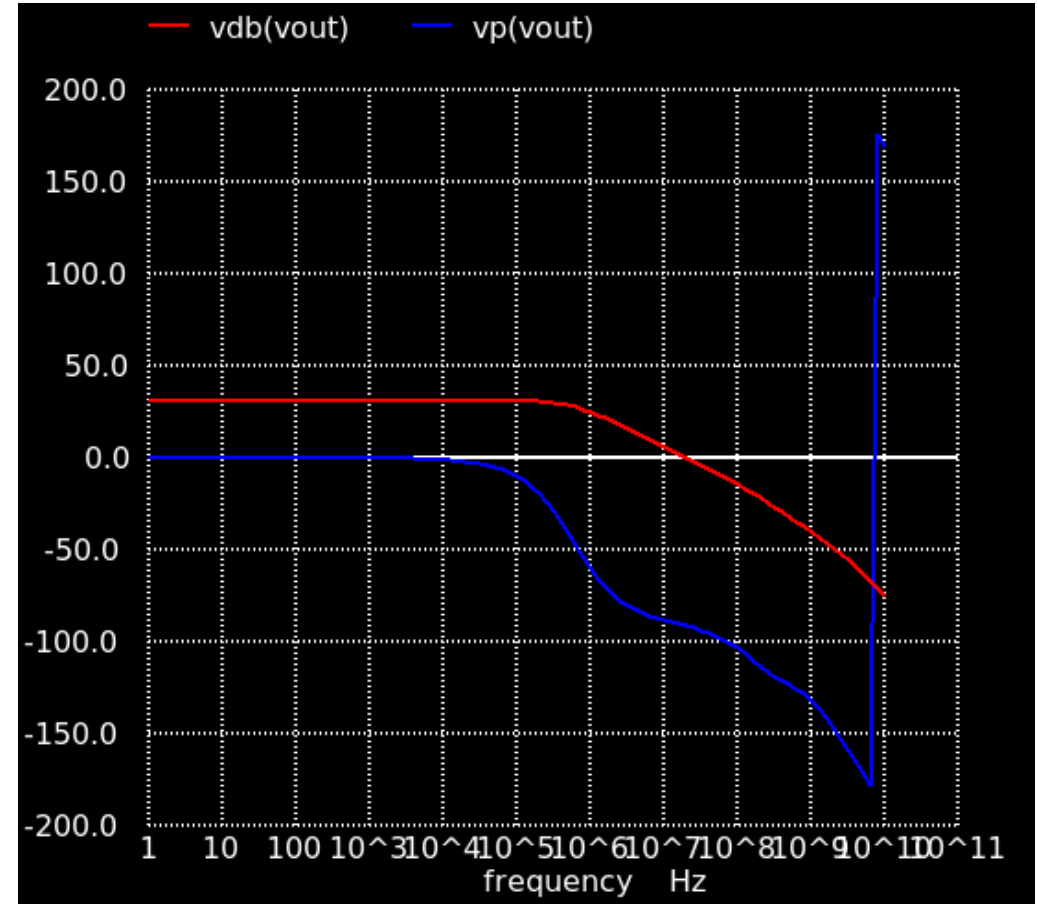
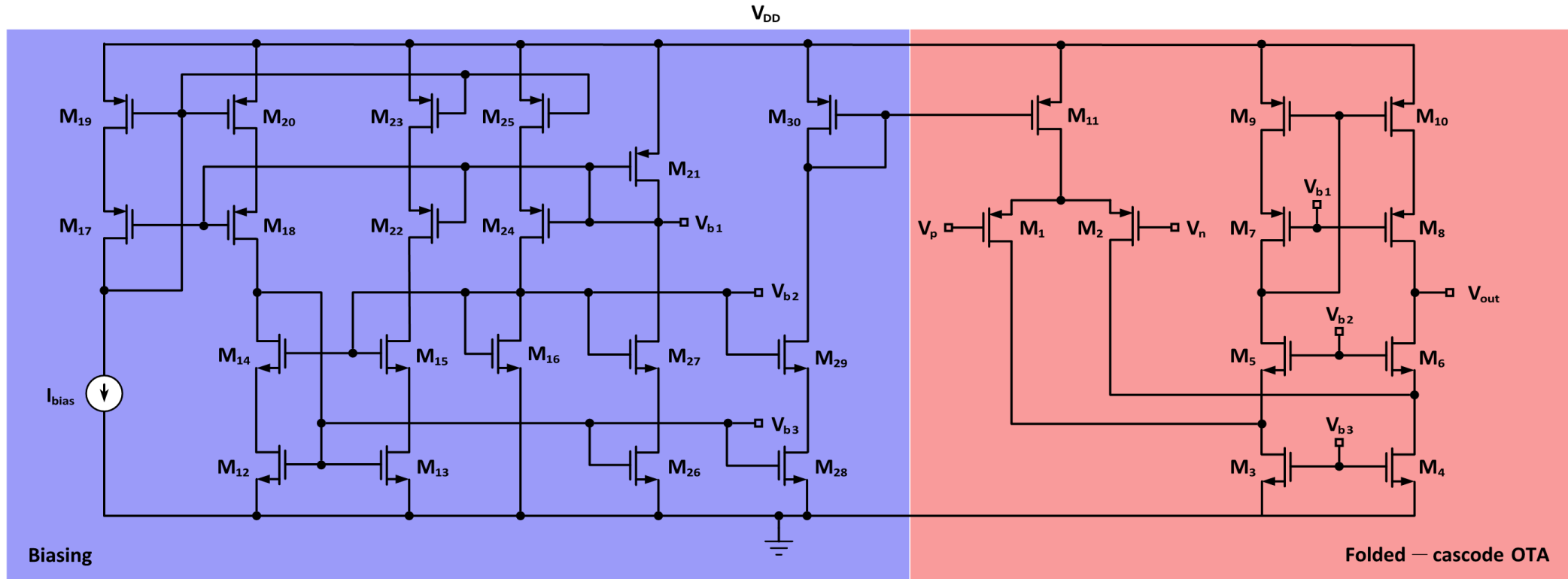


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Folded-cascode OTA with high-swing current mirror biasing

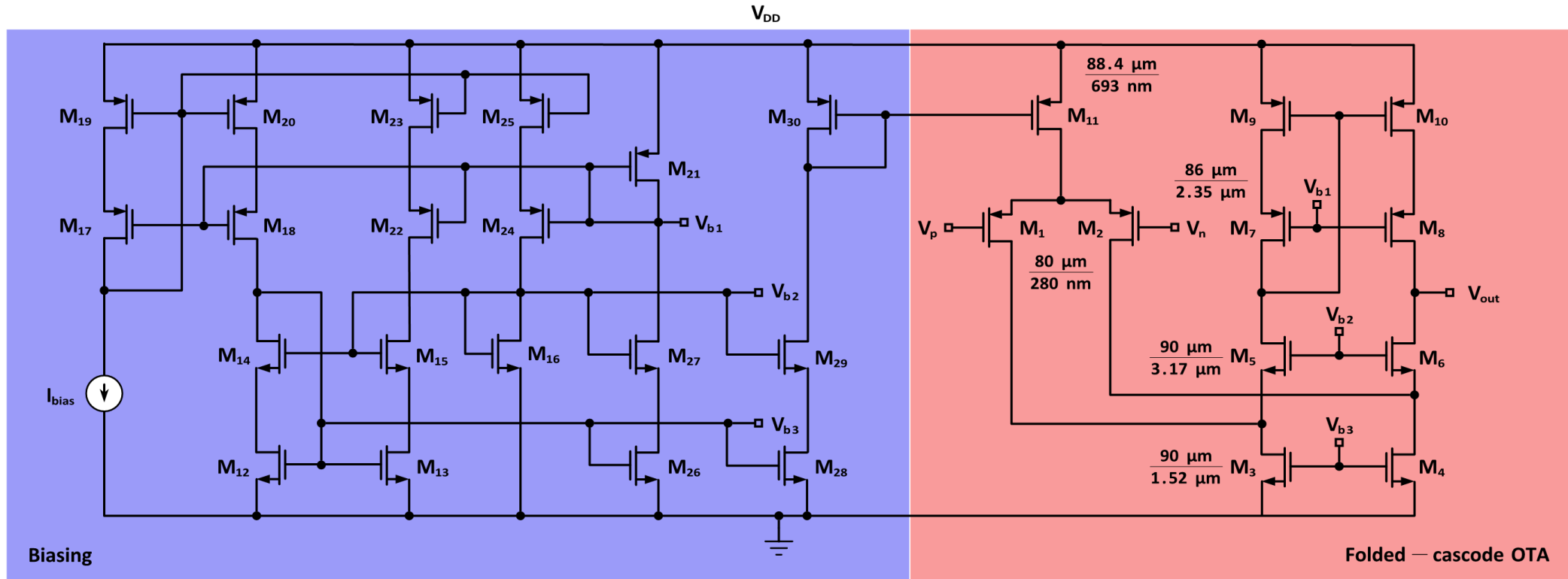


- Specifications:
 - $GBW = 20\text{ MHz}$
 - $C_L = 10\text{ pF}$
- Could be more challenging due to the voltage headroom and more biasing points.

Folded-cascode OTA with high-swing current mirror biasing

- First, start from the folded-cascode OTA design
- Like the design of diff-pair OTA, g_m/i_d method is applied here, so the detailed calculations are omitted here (see previous example).
 - $g_{m,M_1} = 2\pi f_t(1 + 0.2)C_L = 1.5 \text{ mS}$
 - For $M_1 - M_2$, pick $\frac{g_m}{i_d} = 15$, $i_{d,M_1} = \frac{g_{m,M_1}}{\frac{g_m}{i_d}} = 100 \text{ }\mu\text{A}$: $W_{M_1} = 80 \text{ }\mu\text{m}$, $L_{M_1} = 280 \text{ nm}$. Again, if you have gain requirement, you can consider increase L_{M_1} .
 - For $M_7 - M_{10}$, pick $\frac{g_m}{i_d} = 4$, by assuming $i_{d,M_7} = i_{d,M_1} = 100 \text{ }\mu\text{A}$: $W_{M_1} = 86 \text{ }\mu\text{m}$, $L_{M_1} = 2.35 \text{ }\mu\text{m}$.
 - For $M_3 - M_4$, pick $\frac{g_m}{i_d} = 8$, noted that $i_{d,M_3} = i_{d,M_1} + i_{d,M_7} = 200 \text{ }\mu\text{A}$: $W_{M_3} = 90 \text{ }\mu\text{m}$, $L_{M_3} = 1.52 \text{ }\mu\text{m}$.
 - For $M_5 - M_6$, pick $\frac{g_m}{i_d} = 8$, noted that $i_{d,M_5} = i_{d,M_7} = 100 \text{ }\mu\text{A}$: $W_{M_5} = 90 \text{ }\mu\text{m}$, $L_{M_3} = 3.17 \text{ }\mu\text{m}$.
 - For M_{11} , pick $\frac{g_m}{i_d} = 4$, noted that $i_{d,M_{11}} = 2i_{d,M_1} = 200 \text{ }\mu\text{A}$: $W_{M_5} = 88.4 \text{ }\mu\text{m}$, $L_{M_3} = 693 \text{ nm}$.

Folded-cascode OTA with high-swing current mirror biasing

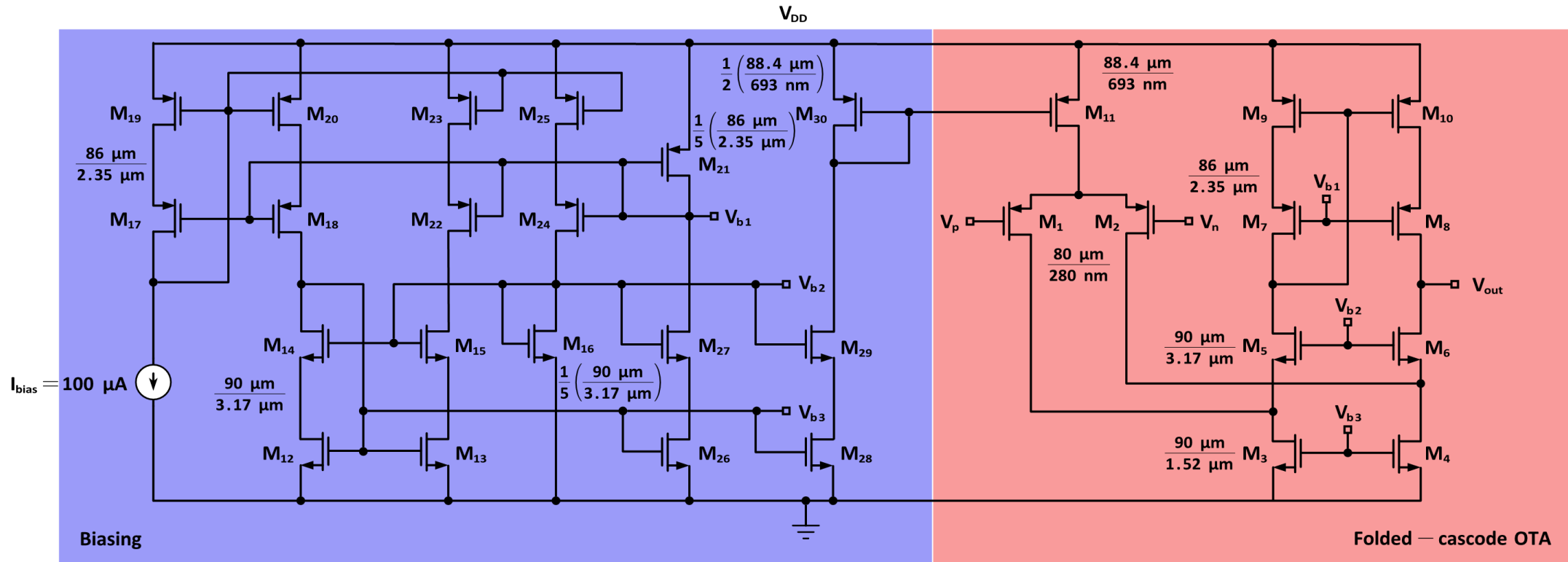


- We next start with designing high-swing current mirror.
 - PMOS high-swing current mirror: $M_{17} - M_{21}$
 - NMOS high-swing current mirror: $M_{12} - M_{16}$

Folded-cascode OTA with high-swing current mirror biasing

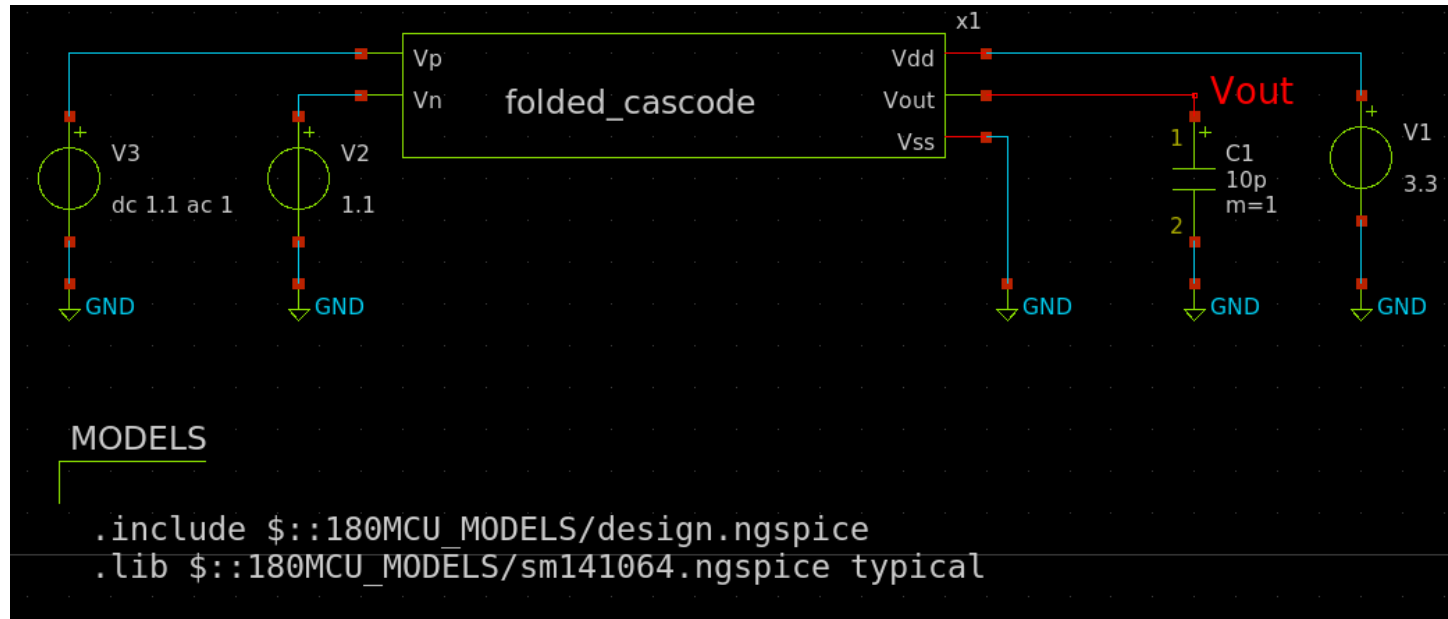
- Similar concept is applied here: passing the same current will ensure the same transconductance, so the biasing point (g_m/i_d) will be the same.
- For PMOS high swing current mirror ($M_{17} - M_{21}$), $M_{17} - M_{20}$ have the same size as M_7 , M_{21} has its length $L_{M_{21}} = 4L_{M_7}$ (or 5 times).
 - $I_{bias} = i_{d,M_7} = 100 \mu A$
- For NMOS high swing current mirror ($M_{12} - M_{16}$), $M_{12} - M_{15}$ have the same size as M_5 , M_{16} has its length $L_{M_{16}} = 4L_{M_5}$ (or 5 times).
- For $M_{22} - M_{25}$, their size can be the same as M_7 .
- For $M_{26} - M_{29}$, their size can be the same as M_5 .
- For M_{29} , $W_{M_{29}} = W_{M_{11}}$, $L_{M_{29}} = 2L_{M_{11}}$.
 - As the current flows through M_{11} is twice of the current through M_3 here.

Folded-cascode OTA with high-swing current mirror biasing



- $V_{b1} = 1.465 \text{ V}, V_{b2} = 1.17 \text{ V}, V_{b3} = 0.876 \text{ V}$
- If you want to replace I_{bias} , you can use constant- g_m method introduced previously (or a BGR).
- Similarly, you can scale down the dimensions of current mirror to reduce their power consumption.

Results



*** SPICE simulations finished! ***

params	gm/id method	SPICE simulation
Id_M1 (uA)	100.53	109.12
Id_M3 (uA)	201.06	198.36
Id_M5 (uA)	100.53	89.24
Id_M7 (uA)	100.53	89.25
Id_M11 (uA)	201.06	218.23
gm/id_M1 (1/V)	15.00	12.71
gm/id_M3 (1/V)	8.00	8.05
gm/id_M5 (1/V)	8.00	8.44
gm/id_M7 (1/V)	4.00	4.54
gm/id_M11 (1/V)	4.00	5.91
gain (dB)	108.61	80.24
GBW (MHz)	20.00	19.95

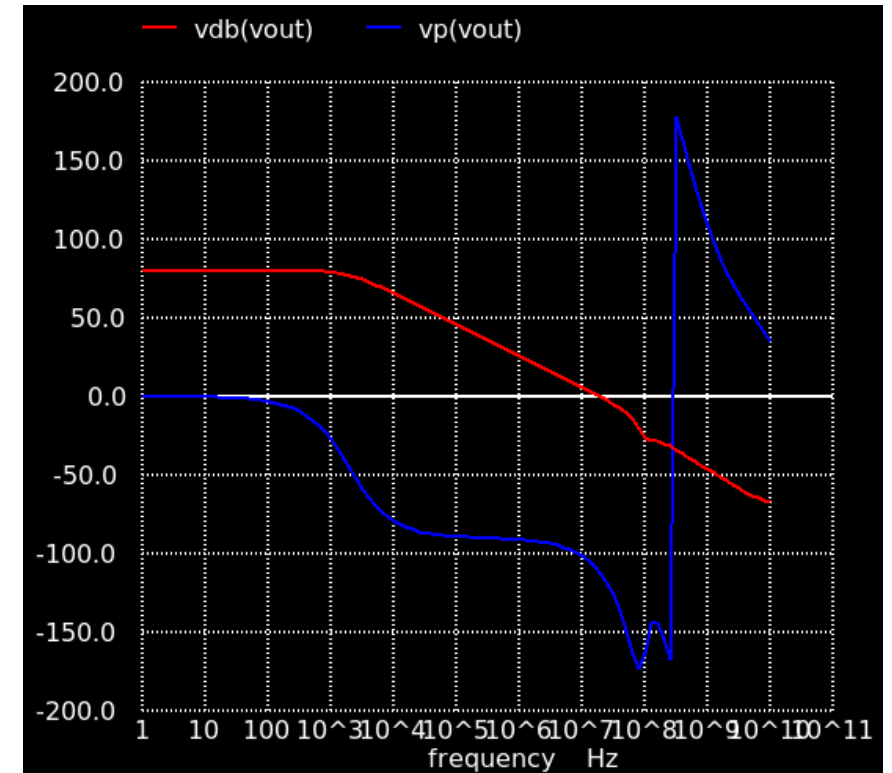
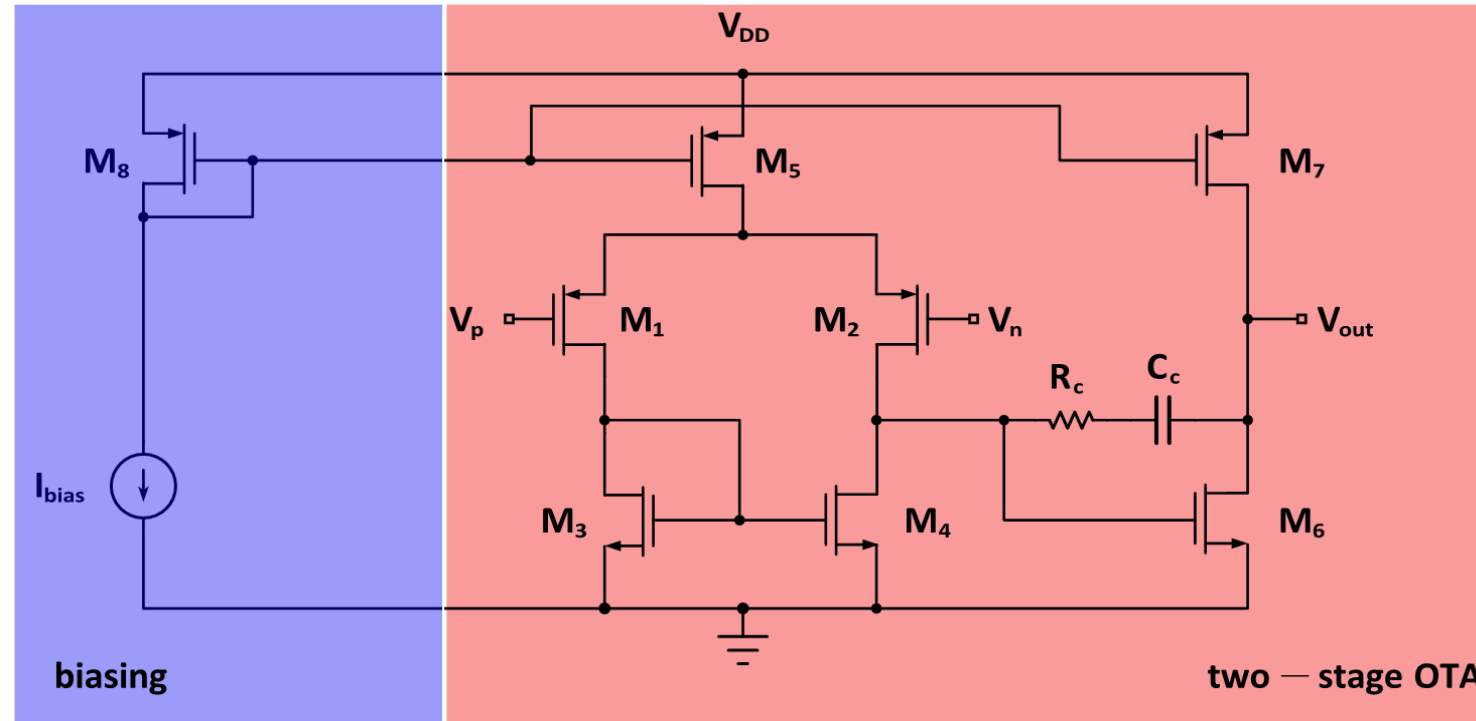


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Two-stage OTA with Miller lead compensation



- Specifications:
 - $GBW = 20\text{ MHz}$
 - $C_L = 10\text{ pF}$

Two-stage OTA with Miller lead compensation

- A few equations are needed here to guide the design here:

- $f_t = \frac{g_m}{2\pi C_c}$

- $C_c \geq 0.22 C_L$ to guarantee at least around 60° PM

- $R_c \approx \frac{1}{1.7 f_t C_c}$ to give you around extra 30° PM

- For removing input-offset voltage: $\frac{\left(\frac{W}{L}\right)_{M_6}}{\left(\frac{W}{L}\right)_{M_4}} = 2 \frac{\left(\frac{W}{L}\right)_{M_7}}{\left(\frac{W}{L}\right)_{M_5}}$

- In case if you have SR requirement: $SR = \frac{I_{M_5}}{C_c}$

Two-stage OTA with Miller lead compensation

- Start with $M_1 - M_2$:
 - For extra margin, we take $C_c = 0.3C_L = 3 \text{ pF}$. This also gives $R_c = 9.8 \text{ k}\Omega$.
 - For extra margin, $g_{m,M_1} = 2\pi f_t(1 + 0.5)C_c = 0.565 \text{ mS}$
 - Pick its $\frac{g_m}{i_d} = 15$, a relatively large value: $i_{d,M_1} = \frac{g_{m,M_1}}{\frac{g_m}{i_d}} = 37.7 \text{ }\mu\text{A}$
 - Pick $W_{M_1} = 30 \text{ }\mu\text{m}$, $L_{M_1} = 280 \text{ nm}$. For two stage OTA, input stage does not need high gain, which is what the second stage is for.

Two-stage OTA with Miller lead compensation

- Second, design active load $M_3 - M_4$
 - Very similar to the design of active load in the diff-pair OTA example, detailed analysis is omitted here.
 - Pick $\frac{g_m}{i_d} = 10$, $W_{M_3} = 31.6 \mu m$, $L_{M_3} = 1.52 \mu m$
- Third, design current source M_5
 - Very similar to the design of current source in the diff-pair OTA example, detailed analysis is omitted here. Just remember $i_{d,M_5} = 2i_{d,M_1}$.
 - Pick $\frac{g_m}{i_d} = 4$, $W_{M_5} = 28.4 \mu m$, $L_{M_5} = 1.1 \mu m$

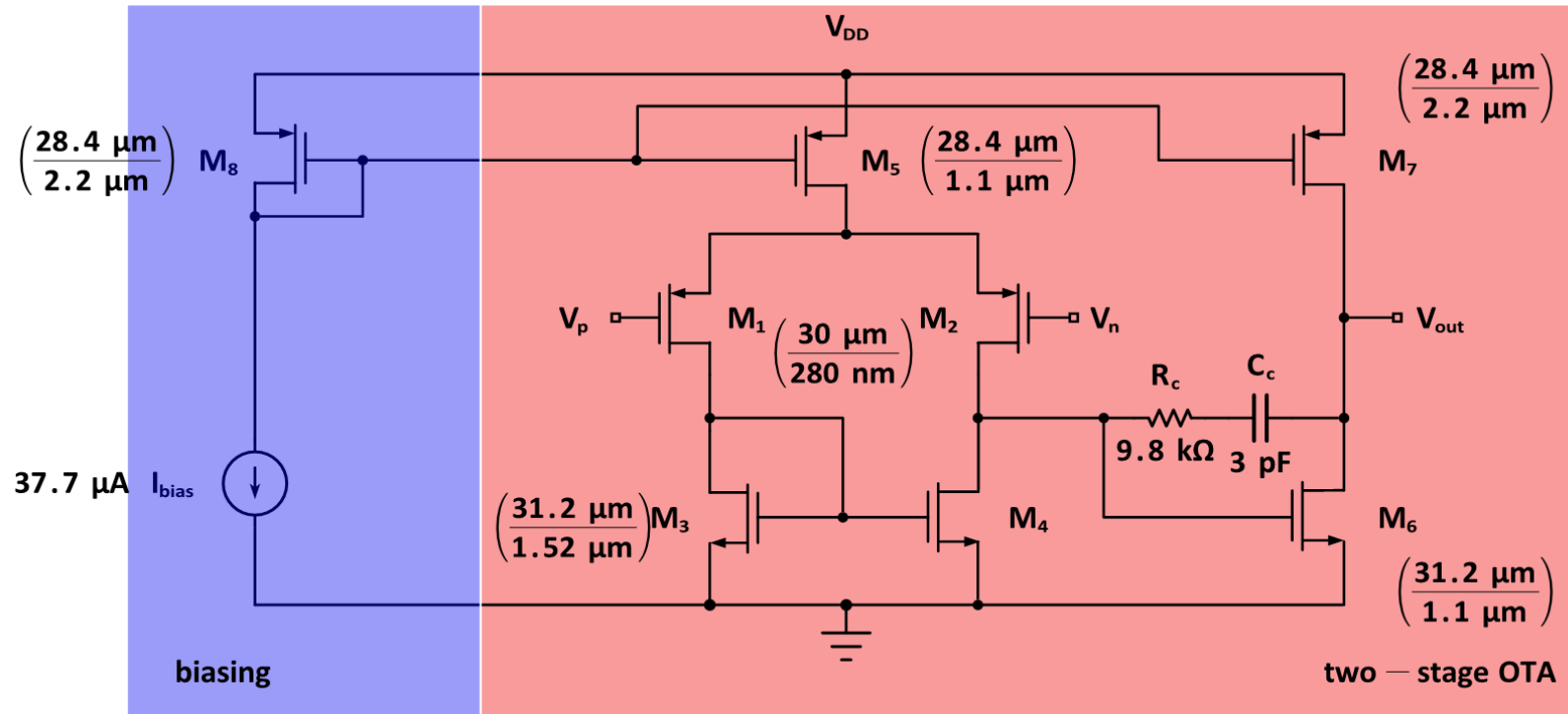
Two-stage OTA with Miller lead compensation

- We now design the second stage. We first start with designing the current source M_7 , as it makes the later current mirror design simpler.
 - We do not have an explicit power budget here, so we assume $i_{d,M_7} = \frac{1}{2} i_{d,M_5} = 37.7 \mu A$.
 - We do not apply normal g_m/i_d method here, since we do not want to violate the input-offset voltage rule. Therefore, we simply do the following sizing for M_7 : $W_{M_7} = W_{M_5} = 28.4 \mu m$, $L_{M_7} = 2L_{M_5} = 2.2 \mu m$.
 - We can reversely check its g_m/i_d now (from $\frac{i_d}{W}$ vs. $\frac{g_m}{i_d}$ plot), which is 6.1, and this is a relatively small number.

Two-stage OTA with Miller lead compensation

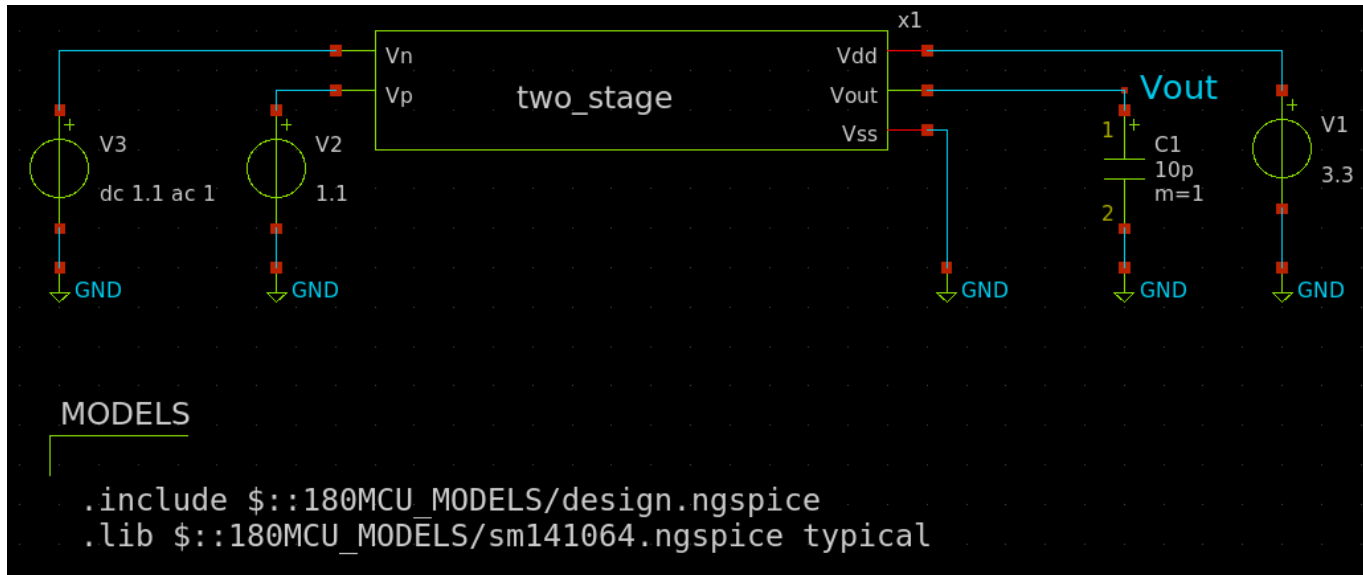
- We then design the gain transistor M_6 of the second stage:
 - Through input-offset sizing relationship: $\left(\frac{W}{L}\right)_{M_6} = 2 \frac{\left(\frac{W}{L}\right)_{M_7}}{\left(\frac{W}{L}\right)_{M_5}} \times \left(\frac{W}{L}\right)_{M_4} = 20.79$
 - We pick $L_{M_6} = 1.1 \mu m$ for some high gain, which leads to $W_{M_6} = 23 \mu m$.
 - We can reversely check its g_m/i_d now (from $\frac{i_d}{W}$ vs. $\frac{g_m}{i_d}$ plot), which is 11, and this is a relatively large number.
- Current mirror transistor M_8 can be the same as M_7 for now.
 - $I_{bias} = 37.7 \mu A$

Two-stage OTA with Miller lead compensation



- If you want to replace I_{bias} , you can use constant- g_m method introduced previously (or a BGR).
- Similarly, you can scale down the dimensions of current mirror to reduce their power consumption.

Results



*** SPICE simulations finished! ***

params	gm/id method	SPICE simulation
Id_M1 (uA)	37.69911184307752	39.95
Id_M3 (uA)	37.69911184307752	39.95
Id_M5 (uA)	75.39822368615503	79.90
Id_M6 (uA)	37.69911184307752	37.96
Id_M7 (uA)	37.69911184307752	37.96
gm/id_M1 (1/V)	15	12.70
gm/id_M3 (1/V)	10	10.51
gm/id_M5 (1/V)	4	4.15
gm/id_M6 (1/V)	10.996805517419196	10.88
gm/id_M7 (1/V)	6.094891296677578	4.12
gain (dB)	83.29207884089496	80.99
GBW (MHz)	20.0	19.95
PM (degree)	-	77.38

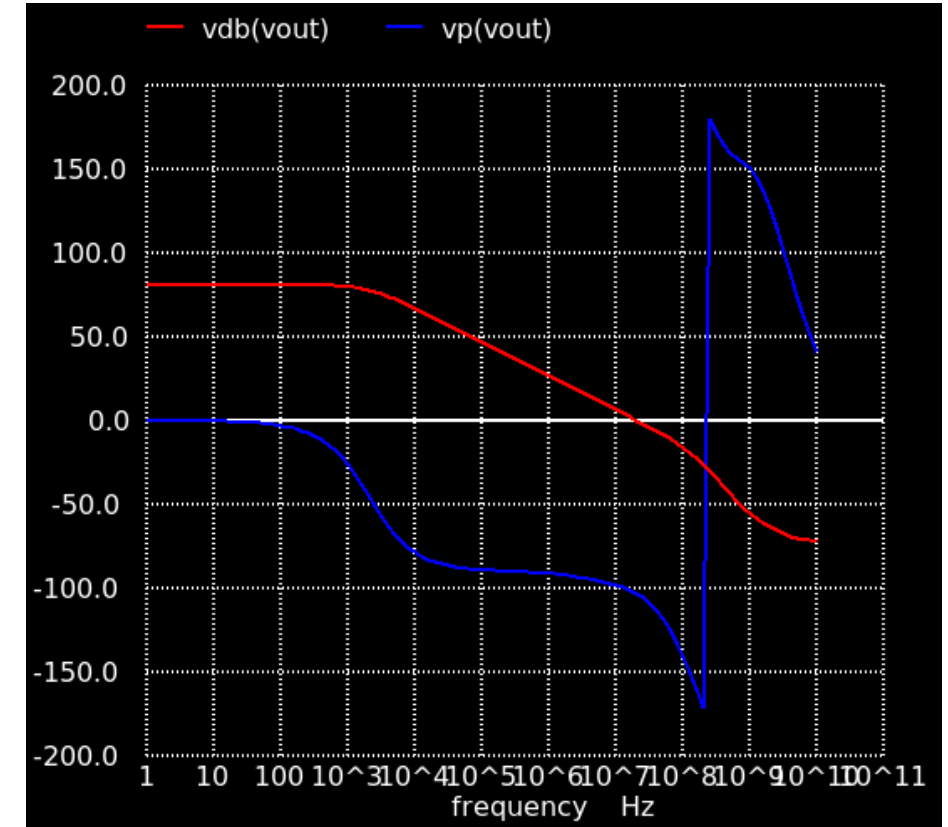


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Conclusion

- A brief introduction of g_m/i_d method is presented.
- Three common OTA circuits are designed using g_m/i_d method in open-source GF180MCU CMOS process.
- Simulation results are very close to the first-order calculations using g_m/i_d method.

References

- Analog Integrated Circuit Design, 2nd Edition
- Paul Allen's lecture notes on two-stage op-amp:
[https://pallen.ece.gatech.edu/Academic/ECE_6412/Spring_2004/L130-OpAmpCompII\(2UP\).pdf](https://pallen.ece.gatech.edu/Academic/ECE_6412/Spring_2004/L130-OpAmpCompII(2UP).pdf)
- Eric Yeh's YouTube video on g_m/i_d method:
<https://www.youtube.com/@ericyeh3787>
- Dr. Hesham Omran's YouTube video on g_m/i_d method:
<https://www.youtube.com/watch?v=dzz4z3ijVts>